

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-6. (Cancelled).

7. (Currently Amended) A semiconductor device, comprising:

a substrate including a plurality of holes and a surface over which an interconnecting pattern is formed, part of the interconnecting pattern being superposed over the holes;

a semiconductor chip disposed over another surface of the substrate and including a plurality of electrodes to be positioned over the holes; and

conductive members provided within the holes for electrically connecting the electrodes to the interconnecting pattern,

~~wherein a recognition hole is formed in the substrate at a position differing from the holes; and~~

~~wherein a recognition pattern is formed over the recognition hole on the side of a surface of the substrate including the interconnecting pattern.~~

8. (Currently Amended) The semiconductor device as defined in claim 7,

~~wherein the recognition hole is formed in the substrate outside a mounting region for the semiconductor chip.~~

9. (Currently Amended) The semiconductor device as defined in claim 7,

~~wherein the recognition pattern includes:~~

a first pattern extending in the X-axis direction of the two-dimensional coordinate system established on a surface of the substrate; and

a second pattern extending in the Y-axis direction.

10-12. (Cancelled).

13. (Currently Amended) A semiconductor device, comprising:
a substrate including a plurality of holes and a surface over which an interconnecting pattern is formed, part of the interconnecting pattern being superposed over the holes;

a semiconductor chip disposed over another surface of the substrate and including a plurality of electrodes to be positioned over the holes; and

conductive members provided within the holes for electrically connecting the electrodes to the interconnecting pattern,

~~wherein~~ the conductive members are a plurality of layered bumps,

~~wherein~~ the bumps include first bumps formed on the electrodes and second bumps formed on the first bumps, and

~~wherein~~ the second bumps are formed of a metal which has a melting point lower than the melting point of the first bumps.

14. (Currently Amended) The semiconductor device as defined in claim 13,
~~wherein~~ the first bumps are formed of gold.

15. (Currently Amended) The semiconductor device as defined in claim 14,
~~wherein~~ the second bumps are formed of solder.

16-33. (Cancelled).